L Number	Hits	Search Text	DB	Time stamp
3	69	electromagnet\$3 same (Gan or (p-type adj	USPAT;	2002/04/22 09:19
		Gan) or (III-V adj nitride))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	60	semiconductor and "hole density" and	USPAT;	2002/04/18 11:36
		nitride and (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj treat\$4))	EPO; JPO;	
			DERWENT;	
-	29	"hole density" and nitride and (anneal\$3	USPAT;	2002/04/18 11:39
		or PTP or RTA or (rapid adj thermal) or	US-PGPUB;	
		(heat adj treat\$4)) and "p-type"	EPO; JPO;	
			DERWENT; IBM TDB	
_	182	("hole density" or "carrier density") and	USPAT;	2002/04/18 11:42
		nitride and (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj treat\$4))	EPO; JPO;	
		and "p-type"	DERWENT;	
_	48	("hole density" or "carrier density") and	IBM_TDB USPAT;	2002/04/18 11:47
	"	nitride and (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj treat\$4))	EPO; JPO;	
		and "p-type" and "III-V"	DERWENT;	
_	186	(("hole density" or "carrier density" or	IBM_TDB USPAT;	2002/04/18 11:51
_	100	resist\$4) same (anneal\$3 or PTP or RTA or	US-PGPUB;	2002/04/16 11.31
		(rapid adj thermal) or (heat adj	EPO; JPO;	
		treat\$4))) and "p-type" and "III-V" and	DERWENT;	
	110	nitride	IBM_TDB	2002/04/18 11:53
_	119	<pre>(("hole density" or "carrier density" or resist\$4) same (anneal\$3 or PTP or RTA or</pre>	USPAT; US-PGPUB;	2002/04/16 11:53
		(rapid adj thermal) or (heat adj	EPO; JPO;	
		treat\$4))) and "p-type" and "III-V" and	DERWENT;	
		nitride and hydrogen	IBM_TDB	0000/04/10 14.35
_	103	(("hole density" or "carrier density" or resist\$4) same (anneal\$3 or PTP or RTA or	USPAT; US-PGPUB;	2002/04/18 14:35
		(rapid adj thermal) or (heat adj	EPO; JPO;	
		treat\$4))) and "p-type" and "III-V" and	DERWENT;	
		nitride and hydrogen and grow\$3	IBM_TDB	0000/04/10 14:47
-	101	(("hole density" or "carrier density" or (resistance or resistivity))) same	USPAT; US-PGPUB;	2002/04/18 14:47
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj	DERWENT;	
		(treat or treated or treating or	IBM_TDB	
		treatment))) and "p-type" and "III-V" and nitride and hydrogen and grow\$3		
_	109	(("hole density" or "carrier density" or	USPAT;	2002/04/18 14:52
		(resistance or resistivity))) same	US-PGPUB;	
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or	DERWENT; IBM TDB	
•		treatment))) and "p-type" and "III-V" and	12.1_12.5	
		nitride and hydrogen		
-	136	(("hole density" or "carrier density" or	USPAT;	2002/04/18 17:10
		<pre>(resistance or resistivity))) same ((anneal or annealed or annealing) or PTP</pre>	US-PGPUB; EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj	DERWENT;	
		(treat or treated or treating or	IBM_TDB	
		treatment))) and (p-type adj GaN)		0000/04/10 15:01
-	14	07/970,145	USPAT;	2002/04/18 15:04
j			US-PGPUB; EPO; JPO;	
•			DERWENT;	
	ļ		IBM_TDB	
-	0	07/970,145.rlan.	USPAT;	2002/04/18 15:04
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	2	970,145.ap.	USPAT;	2002/04/18 15:04
			US-PGPUB;	
ļ			EPO; JPO;	
			DERWENT; IBM TDB	
_	92	(("hole density" or "carrier density" or	USPAT;	2002/04/18 17:13
	, , ,	(resistance or resistivity))) same	US-PGPUB;	2002/04/18 17:13
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj	DERWENT;	
		(treat or treated or treating or	IBM TDB	
		treatment))) and (p-type adj GaN) and	-	
		(etch or etching or etchant)		
-	96	(("hole density" or "carrier density" or	USPAT;	2002/04/19 09:22
		(resistance or resistivity)) same (etch or	US-PGPUB;	
		etching or etchant or plasma)) and (p-type adj GaN)	EPO; JPO; DERWENT;	
		auj Gan,	IBM TDB	
_	34	(("hole density" or "carrier density" or	USPAT;	2002/04/19 09:19
		(resistance or resistivity)) same (etch or	US-PGPUB;	2002, 01, 13 03.13
1 -		etching or etchant or plasma)) same	EPO; JPO;	
		(p-type adj GaN)	DERWENT;	
			IBM_TDB	
-	181		USPAT;	2002/04/19 13:28
		same (p-type adj GaN)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-	96	(("hole density" or "carrier density" or	USPAT;	2002/04/19 09:20
		(resistance or resistivity)) same (etch or	US-PGPUB;	2002, 01, 13
		etching or etchant or plasma)) and (p-type	EPO; JPO;	
		adj GaN)	DERWENT;	
		,	IBM_TDB	
-	100	' '	USPAT;	2002/04/19 09:26
		(resistance or resistivity)) same (clean	US-PGPUB;	
		or cleaned or cleaning or koh or naoh or nh4oh etch or etching or etchant or	EPO; JPO; DERWENT;	
		plasma)) and (p-type adj GaN)	IBM TDB	
_	22		USPAT;	2002/04/19 09:31
		GaN)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/04/10 00 01
_	314	(koh or naoh or nh4oh) and GaN	USPAT;	2002/04/19 09:31
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	31	(koh or naoh or nh4oh) same GaN	USPĀT;	2002/04/19 10:16
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
1_	2159	(GaN or (p-type adj GaN) or "III-V" or	IBM_TDB USPAT;	2002/04/19 13:10
-	2139	(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	2002/04/19 13.10
		same (etch or etching or etchant or Naoh	EPO; JPO;	
		or Koh)	DERWENT;	
		·	IBM_TDB	
-	146	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 11:04
		(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	
		same (etch or etching or etchant or Naoh	EPO; JPO;	
		or Koh) same (resistivity or resistance)	DERWENT; IBM TDB	
_	9	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 10:34
		(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	
·		same (etch or etching or etchant or Naoh	EPO; JPO;	
		or Koh) same (resistivity or resistance)	DERWENT;	
		same hydrogen	IBM_TDB	

Gan or (p-type ad) Gan) or AlInGan or AlGan Same (passivation or passivating or passivate) Same (passivation or passivating or gallium adj nitride) or AlInGan or AlGan Same yassivation or passivating or passivation or passivating or passivate) same (hydrogen or h or h2) SPO; JPO; DERWENT; IBM TDB Same (passivation or passivating or passivation or passivating or passivation or passivating or passivation or passivating or passivation same (passivation or passivating or passivation or pa					
same (passivation or passivating or passivating or passivate) Same (passivate) Same (passivation or passivating or (gallium adj nitride) or AlInGan or AlGaN) same (passivation or passivating or passivation or passivating or passivation or passivating or passivation or pa	-	412	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 10:35
passivate) [Saw or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (passivation or passivating or passivate) same (hydrogen or h or h2) same (passivation or passivating or passivate) same (hydrogen or h or h2) same (gallium adj nitride) or AlInGan or AlGaN) same (passivation or passivating or passivate) same (hydrogen or h or h2) same (Etch or etchant or etching) same (Etch or etchant or etching) same (fight) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (hydrogen or h) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj same resistivity same (san or (p-type adj SaN) or "III-V" or (sallium adj nitride) or AlInGan or AlGaN) same (surface adj same resistivity same (san or (p-type adj SaN) or "III-V" or same resistivity same (san or (p-type adj SaN) or "III-V" or nitride" or (gaN) or "III-V" or nitride" or (gaN) or "III-V" or nitride) or Same resistivity same ((p-type adj SaN) or "III-V" or nitride" or Same resistivity same ((p-type adj SaN) or "III-V" or hydrogen) same resistivity same ((p-type adj SaN) or "III-V") [Cetch or etching or etchant or plasma) same resistivity same ((p-type adj SaN) or "III-V") [Cetch or etching or etchant or plasma) same resistivity same ((p-type adj SaN) or "III-V") [Cetch or etching or etchant or plasma) same resistivity same ((p-type adj SaN) or "III-V") [Cetch or etching or etchant or plasma) same resistivity same ((p-type adj SaN) o	,		(gallium adi nitride) or AlInGan or AlGaN)		
Solution					
S8			passivate)	i i	
Can or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) Same (passivation or passivating or passivate) same (hydrogen or hor hor hor hor hor management of the passivate) same (passivating or passivating or passivating or passivate) same (passivating or passivating or passivating or passivate) same (hydrogen or h or hor hor hor hor passivate) same (for or etchind) Same (for or etch		50	(C-N on /n time add CaN) or "III-V" or	- 1	2002/04/19 10:37
same (passivation or passivating or passivating or passivate) same (hydrogen or h or h2) [GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (passivation or passivating or passivate) same (hydrogen or h or h2) same (Etch or etchant or etching) [Etch or etchant or etching] [GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same ((hydrogen or h) adj remov\$3) [GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj uspār; uspār; uspār) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj uspār; uspār) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj uspār) [GaN or (p-type adj GaN) or "III-V adj uspār; uspār) [GaN or (p-type adj GaN) or "III-V adj uspār; uspār) [GaN or (gallium adj nitride) or AlInGan or AlGaN) uspār; uspār] [GaN or (p-type adj GaN) or "III-V adj uspār; uspār] [GaN or (gallium adj nitride) or AlInGan or AlGaN) uspār; uspār] [GaN or (gallium adj nitride) or AlInGan or AlGaN) uspār; uspār] [GaN or (gallium adj nitride) or AlInGan or AlGaN) uspār; uspār] [GaN or (gallium adj nitride) or AlInGan or AlGaN) uspār; uspār] [GaN or (gallium adj nitride) or GaN or (gallium adj nitride) or (gallium adj nitride) or (gallium adj nitride) or (gallium adj nitride) or (galli	-	58	(Gan or (p-type adj Gan) of fire of AlGan)		
Derwent			came (passivation or passivating or	·	
Can or (p-type adj Gan) or "III-V" or (gallium adj nitride) or AlInGan or AlGan) Same (passivation or passivating or passivate) same (hydrogen or h or h2) same (Etch or etchant or etching) US-PGPUB; Same (GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGan) Same ((hydrogen or H) adj remov\$3) US-PGPUB; Same (surface adj treat\$4) US-PGPUB; Same (adj US-PGPUB; Same resistivity (adj US-PGPUB; Same resistivity (adj US-PGPUB; Same resistivity same (adj US-PGPUB; Same) (adj US-PGPUB;			passivate) same (hydrogen or h or h2)	·	
Comparison of Alingan or Algan Comparison of Algan Compariso			passivato, same (injunity)	IBM_TDB	
Gallium adj nitride) or AlInGan or AlGaN) Same (passivation or passivating or passivation) or passivating or passivating or passivate) same (hydrogen or h or h2) same (Etch or etchant or etching) (GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) Same (hydrogen or h) adj remov\$3) Same (surface adj treat\$4) Same (surface adj treat\$4) Same (surface adj treat\$4) Same (surface adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same (surface adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same resistivity Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same resistivity Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) Same resistivity Same (surface adj or "III-V" adj nitride" or (gallium adj nitride) or Epro, JPO; DERWENT; IBM TDB Same resistivity same (gan or (p-type adj GaN) Sapar; Same resistivity same (sapar) Sapar; S	_	10	(GaN or (p-type adj GaN) or "III-V" or		2002/04/19 10:42
passivate) same (hydrogen or h or h2) same (Etch or etchant or etching) (GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same ((hydrogen or h) adj remov\$3) SPAT; USPAT;			(gallium adj nitride) or AlInGan or AlGaN)	· · · · · · · · · · · · · · · · · · ·	•
CEtch or etchiant or etching or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) Same ((hydrogen or H) adj remov\$3) Same (surface adj treat\$4) Same (surface adj nitride) or AlInGan or AlGaN) same (Naoh or Koh or AlInGan or AlGaN) same (Naoh or Koh or AlInGan or AlGaN) same (Naoh or Koh or AlInGan or AlGaN) same (surface adj nitride) Same resistivity Same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj same resistivity same (san or (p-type adj san or "III-V") Same resistivity same (san or (p-type adj san or "III-V") Same resistivity same (san or (p-type adj san) san or "III-V") San or "III-V")	']	same (passivation or passivating or		
Can or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGan) same (hydrogen or H) adj remov\$3)			passivate) same (hydrogen or h or h2) same	· I	
(gallium adj nitride) or AlInGan or AlGaN) same ((hydrogen or H) adj remov\$3) (GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) (GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) (GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) (GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (Naoh or Koh or nh4oh) (etch or etching or etchant or plasma) same resistivity (etch or etching or etchant or plasma) same resistivity same (GaN or (p-type adj GaN) or "III-V" or nitride) (etch or etching or etchant or plasma) same resistivity same (fp-type adj GaN) or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V")	ļ		(Etch or etchant or etching)		2002/04/19 10:43
same ((hydrogen or H) adj remov\$3) - 87 (GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) - 25 (GaN or (p-type adj GaN) or "III-V adj USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USP	-	4	(Gan or (p-type ad) Gan) of III-V or		2002/01/20 2011
Can or (p-type adj Gan) or "III-V" or (gallium adj nitride) or AlInGan or AlGan) Same (surface adj treat\$4) September			same (thydrogen or H) adi remov\$3)		
GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4)			Same (mydrogen or m, day remains,	DERWENT;	
(Gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) [GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (Naoh or Koh or Naoh or Nahoh) [Gan or AlGan) same (Naoh or Koh or Nahoh) [Catch or etching or etchant or plasma) same resistivity [Catch or etching or etchant or plasma) same resistivity same (GaN or (p-type adj GaN) or "III-V" or nitride) [Catch or etching or etchant or plasma) same resistivity same (Gan or (p-type adj Gan) or "III-V") [Catch or etching or etchant or plasma) same resistivity same ((p-type adj Gan) or "III-V") [Catch or etching or removing or plasma) same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma) same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma] same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma] same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma] same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma] same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma] same resistivity same ((p-type adj Gan) or "III-V") [Catch or cleaning or removing or plasma] same resistivity same ((p-type adj Gan) same resistivity same ((p-type adj Gan) or "III-V")			•	_	
(gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) - 25 (GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	_	87	(GaN or (p-type adj GaN) or "III-V" or		2002/04/19 11:45
Can or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JP			(gallium adj nitride) or AlInGan or AlGaN)		
Can or (p-type adj Gan) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGan) same (surface adj treat\$4)			<pre>same (surface adj treat\$4)</pre>		
GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (surface adj treat\$4) (GaN or (p-type adj GaN) or "III-V adj treat\$4) (GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGan or AlGaN) same (Naoh or Koh or nh4oh) (Gan or etching or etchant or plasma) same resistivity (Gan or etching or etchant or plasma) same resistivity same (GaN or (p-type adj GaN) or "III-V" or nitride) (Gan or (p-type adj GaN) or "III-V" or nitride) (Gan or (p-type adj GaN) or "III-V" or nitride) (Gan or (p-type adj GaN) or "III-V") (Gan or "III-V") (Gan or (p-type adj GaN) or "III-V") (Gan or "III-V") (Gan or (p-type adj GaN) or "III-V") (Gan or "III-V") (Gan or (p-type adj GaN) or "III-V") (Gan or "III-V") (Gan or "III-V") (Gan or (p-type adj GaN) or "III-V") (Gan or			•		
Comparison of (p-type add) and positive of the property of t		0.5	(G.V. a.v. /a tumo add CaN) or "TIT-V add		2002/04/19 11:47
Alingan or Algan) same (surface adj treat\$4) - 32 (GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or Alingan or Algan) same (Naoh or Koh or nh4oh) - 6756 (etch or etching or etchant or plasma) same resistivity - 1016 (etch or etching or etchant or plasma) same resistivity same (GaN or (p-type adj GaN) or "III-V" or nitride) - 33 (etch or etching or etchant or plasma) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V")	-	25	nitride" or (gallium adi nitride) or		
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Clean or (p-type ad) GaN) of ritide Or (mitride" or (gallium adj nitride) or AlInGan or AlGaN) same (Naoh or Koh or nh4oh) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EP			· · · ·		
AlInGan or AlGaN) same (Naoh or Koh or nh4oh) (etch or etching or etchant or plasma) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IMD_TDB USPAT; US-PGPUB; IMD_TDB USPAT;	_	32	(GaN or (p-type adj GaN) or "III-V adj	3	2002/04/19 13:11
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	İ		nitride" or (gallium adj nitride) or		
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same resistivity Comparison of the company of th		6756	(atch or etching or etchant or plasma)	_	2002/04/19 13:29
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- 1016 (etch or etching or etchant or plasma) same resistivity same (GaN or (p-type adj GaN) or "III-V" or nitride) - 33 (etch or etching or etchant or plasma) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") - 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V")	1		J		
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GaN) or "III-V" or nitride) [EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; DE	-	1016	(etch or etching or etchant or plasma)		2002/01/19 10:01
- 33 (etch or etching or etchant or plasma) same resistivity same ((p-type adj GaN) or GaN or "III-V") 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 59 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 50 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V")	.		same resistivity same (Gan of the type add)	1	
- 33 (etch or etching or etchant or plasma) same resistivity same ((p-type adj GaN) or GaN or "III-V") 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 2002/04/19 13			Gan) or "III-V of Hittide)		
cetch or etching of etchant of plasma, same resistivity same ((p-type adj GaN) or GaN or "III-V") 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V") 59 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V")					
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or GaN or "III-V") Septimization of the content			same resistivity same ((p-type adj GaN)		
clean or cleaning or removing or hydrogen) same resistivity same ((p-type adi GaN) or GaN or "III-V") IBM_TDB USPAT; US-PGPUB; EPO; JPO;			or GaN or "III-V")		
_ 58 (clean or cleaning or removing or hydrogen) same resistivity same ((p-type adi GaN) or GaN or "III-V")					
hydrogen) same resistivity same ((p-type us-PGPUB; adi GaN) or GaN or "III-V")			(aloan or cleaning or removing or	· –	2002/04/19 13:36
adi GaN) or GaN or "III-V") EPO; JPO;	-	58	hydrogen) same resistivity same ((p-type	5	
DERWENT:			adi GaN) or GaN or "III-V")	EPO; JPO;	
				DERWENT;	
IBM_TDB 2003/04/19 13					2002/04/19 13:48
d (clean or cleaning of felloving) same	-	9	(clean or cleaning or removing) same		2002/04/19 13:40
resistivity same ((p-type adj GaN) or GaN US-FG-US)			resistivity same ((p-type adj GaN) or GaN	1	
or "III-V")			or "III-V")	· ·	
IBM TDB					
(chemical add treatment) same resistivity USPAT; 2002/04/19 13		1	(chemical adj treatment) same resistivity	· —	2002/04/19 13:48
same ((p-type adj GaN) or GaN or "III-V") US-PGPUB;	1		same ((p-type adj GaN) or GaN or "III-V")	1	
EPO; JPO;					
DERWENT;					
1' 1 -			1 (G-N CoN on Un-time CaMU or	_	2002/04/19 13:55
clean and (GaN or p-GaN or "p-type GaN" or USPAT; 2002/04/19 13 "III-V nitride" or p-type) USPAT; 2002/04/19 13	-	3554	clean and (Gan or p-dan or p-type dan of	1	
EPO; JPO;			"III-A HILLING OT b.chbel	EPO; JPO;	
DERWENT;		1			
IBM TDB	1			IBM TDB]

	247	clean and (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type) and (koh or	USPAT; US-PGPUB;	2002/04/19 13:58
		naoh or nh4oh)	EPO; JPO; DERWENT;	
	20	<pre>clean same (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type) and (koh or</pre>	IBM_TDB USPAT; US-PGPUB;	2002/04/19 14:15
		naoh or nh4oh)	EPO; JPO; DERWENT;	
	134	plasma same (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type) and (koh or	IBM_TDB USPAT; US-PGPUB;	2002/04/19 17:27
		naoh or nh4oh)	EPO; JPO; DERWENT; IBM TDB	
	3	022,364.ap.	USPAT; US-PGPUB; EPO; JPO;	2002/04/19 14:22
			DERWENT; IBM_TDB USPAT;	2002/04/19 14:23
	3	020,629.ap.	US-PGPUB; EPO; JPO;	2002/04/15 11:20
	0	"Etching adj GaN" and "DC adj plasma"	DERWENT; IBM_TDB USPAT;	2002/04/19 14:24
•		Doming and and	US-PGPUB; EPO; JPO; DERWENT;	
-	641	ultrasonic\$3 and clean\$3 and (Gan or	IBM_TDB USPAT; US-PGPUB;	2002/04/19 16:47
		(p-type adj Gan) or p-type)	EPO; JPO; DERWENT; IBM TDB	
-	108	ultrasonic\$3 and clean\$3 same (Gan or (p-type adj Gan) or p-type)	USPAT; US-PGPUB; EPO; JPO;	2002/04/19 16:47
			DERWENT; IBM_TDB	2002/04/19 16:50
-	32	ultrasonic\$3 same clean\$3 same (Gan or (p-type adj Gan) or p-type)	USPAT; US-PGPUB; EPO; JPO;	2002/04/19 10.50
	_	ultrasonic\$3 same clean\$3 same (Gan or	DERWENT; IBM_TDB USPAT;	2002/04/19 16:51
-	5	(p-type adj Gan))	US-PGPUB; EPO; JPO; DERWENT;	
_	16	ultrasonic\$3 same (Gan or (p-type adj	IBM_TDB USPAT; US-PGPUB;	2002/04/19 16:52
		Gan))	EPO; JPO; DERWENT;	
-	563	ultrasonic\$3 same (Gan or (p-type adj Gan) or nitride)	05 101027	2002/04/19 16:5
		OI MICIACO,	EPO; JPO; DERWENT; IBM TDB	
-	16	ultrasonic\$3 same (Gan or (p-type adj Gan) or (III-V adj nitride))	USPĀT; US-PGPUB; EPO; JPO;	2002/04/22 09:1
		ultrasonic\$3 same (Gan or (p-type adj Gan)	DERWENT; IBM_TDB USPAT;	2002/04/19 16:5
-	30	or (III-V))	US-PGPUB; EPO; JPO; DERWENT;	
			IBM TDB	

	plasma same (GaN or p-GaN or "p-type GaN" or "III-V nitride") and (koh or naoh or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/19 17:28
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